

4N29M, 4N30M, 4N32M, 4N33M, H11B1M, TIL113M General Purpose 6-Pin Photodarlington Optocoupler

Features

- High sensitivity to low input drive current
- Meets or exceeds all JEDEC Registered Specifications
- UL, C-UL approved, File #E90700, Volume 2
- IEC 60747-5-2 approved (ordering option V)

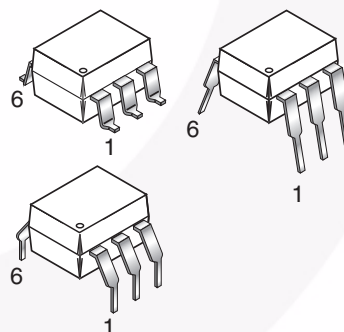
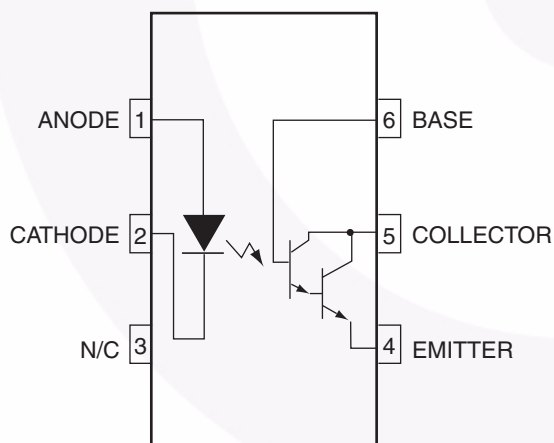
Applications

- Low power logic circuits
- Telecommunications equipment
- Portable electronics
- Solid state relays
- Interfacing coupling systems of different potentials and impedances

Description

The 4N29M, 4N30M, 4N32M, 4N33M, H11B1M and TIL113M have a gallium arsenide infrared emitter optically coupled to a silicon planar photodarlington.

Schematic



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise specified.)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Value	Units
TOTAL DEVICE			
T _{STG}	Storage Temperature	-50 to +150	°C
T _{OPR}	Operating Temperature	-40 to +100	°C
T _{SOL}	Lead Solder Temperature (Wave)	260 for 10 sec	°C
P _D	Total Device Power Dissipation @ T _A = 25°C Derate above 25°C	250	mW
		3.3	mW/°C
EMITTER			
I _F	Continuous Forward Current	80	mA
V _R	Reverse Voltage	3	V
I _{F(pk)}	Forward Current – Peak (300μs, 2% Duty Cycle)	3.0	A
P _D	LED Power Dissipation @ T _A = 25°C Derate above 25°C	150	mW
		2.0	mW/°C
DETECTOR			
BV _{CEO}	Collector-Emitter Breakdown Voltage	30	V
BV _{CBO}	Collector-Base Breakdown Voltage	30	V
BV _{ECO}	Emitter-Collector Breakdown Voltage	5	V
P _D	Detector Power Dissipation @ T _A = 25°C Derate above 25°C	150	mW
		2.0	mW/°C
I _C	Continuous Collector Current	150	mA

Electrical Characteristics (T_A = 25°C Unless otherwise specified.)

Individual Component Characteristics

Symbol	Parameter	Test Conditions	Device	Min.	Typ.	Max.	Unit
EMITTER							
V _F	Input Forward Voltage*	I _F = 10mA	4NXXM		1.2	1.5	V
			H11B1M, TIL113M	0.8	1.2	1.5	
I _R	Reverse Leakage Current*	V _R = 3.0V	4NXXM		0.001	100	μA
		V _R = 6.0V	H11B1M, TIL113M		0.001	10	
C	Capacitance*	V _F = 0V, f = 1.0MHz	All		150		pF
DETECTOR							
BV _{CEO}	Collector-Emitter Breakdown Voltage*	I _C = 1.0mA, I _B = 0	4NXXM, TIL113M	30	60		V
			H11B1M	25	60		
BV _{CBO}	Collector-Base Breakdown Voltage*	I _C = 100μA, I _E = 0	All	30	100		V
BV _{ECO}	Emitter-Collector Breakdown Voltage*	I _E = 100μA, I _B = 0	4NXXM	5.0	10		V
			H11B1M, TIL113M	7	10		
I _{CEO}	Collector-Emitter Dark Current*	V _{CE} = 10V, Base Open	All		1	100	nA

Transfer Characteristics

Symbol	Parameter	Test Conditions	Device	Min.	Typ.	Max.	Unit
DC CHARACTERISTICS							
I _{C(CTR)}	Collector Output Current ^{*(1, 2)}	I _F = 10mA, V _{CE} = 10V, I _B = 0	4N32M, 4N33M	50 (500)			mA (%)
			4N29M, 4N30M	10 (100)			
		I _F = 1mA, V _{CE} = 5V	H11B1M	5 (500)			
		I _F = 10mA, V _{CE} = 1V	TIL113M	30 (300)			
V _{CE(SAT)}	Saturation Voltage ^{*(2)}	I _F = 8mA, I _C = 2.0mA	4NXXM			1.0	V
			TIL113M			1.25	
		I _F = 1mA, I _C = 1mA	H11B1M			1.0	
AC CHARACTERISTICS							
t _{on}	Turn-on Time	I _F = 200mA, I _C = 50mA, V _{CC} = 10V, R _L = 100Ω	4NXXM, TIL113M			5.0	μs
		I _F = 10mA, V _{CE} = 10V, R _L = 100Ω	H11B1M		25		
t _{off}	Turn-off Time	I _F = 200mA, I _C = 50mA, V _{CC} = 10V, R _L = 100Ω	4N32M, 4N33M, TIL113M			100	μs
			4N29M, 4N30M			40	
		I _F = 10mA, V _{CE} = 10V, R _L = 100Ω	H11B1M		18		
BW	Bandwidth ^(3, 4)				30		kHz

Electrical Characteristics ($T_A = 25^\circ\text{C}$ Unless otherwise specified.) (Continued)**Isolation Characteristics**

Symbol	Characteristic	Test Conditions	Device	Min.	Typ.	Max.	Units
V_{ISO}	Input-Output Isolation Voltage ⁽⁵⁾	$f = 60\text{Hz}$, $t = 1 \text{ sec.}$	All	7500			V_{AC}^{PEAK}
		VDC	4N32M*	2500			V
		VDC	4N33M*	1500			
R_{ISO}	Isolation Resistance ⁽⁵⁾	$V_{I-O} = 500\text{VDC}$	All	10^{11}			Ω
C_{ISO}	Isolation Capacitance ⁽⁵⁾	$V_{I-O} = \emptyset$, $f = 1\text{MHz}$	All		0.8		pF

* Indicates JEDEC registered data.

Notes:

1. The current transfer ratio (I_C/I_F) is the ratio of the detector collector current to the LED input current.
2. Pulse test: pulse width = $300\mu\text{s}$, duty cycle $\leq 2.0\%$.
3. I_F adjusted to $I_C = 2.0\text{mA}$ and $I_C = 0.7\text{mA rms}$.
4. The frequency at which I_C is 3dB down from the 1kHz value.
5. For this test, LED pins 1 and 2 are common, and phototransistor pins 4, 5 and 6 are common.

Safety and Insulation Ratings

As per IEC 60747-5-2, this optocoupler is suitable for “safe electrical insulation” only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Symbol	Parameter	Min.	Typ.	Max.	Unit
	Installation Classifications per DIN VDE 0110/1.89 Table 1				
	For Rated Main Voltage < 150Vrms		I-IV		
	For Rated Main voltage < 300Vrms		I-IV		
	Climatic Classification		55/100/21		
	Pollution Degree (DIN VDE 0110/1.89)		2		
CTI	Comparative Tracking Index	175			
V_{PR}	Input to Output Test Voltage, Method b, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with $t_m = 1 \text{ sec}$, Partial Discharge < 5pC	1594			V_{peak}
	Input to Output Test Voltage, Method a, $V_{IORM} \times 1.5 = V_{PR}$, Type and Sample Test with $t_m = 60 \text{ sec}$, Partial Discharge < 5pC	1275			V_{peak}
V_{IORM}	Max. Working Insulation Voltage	850			V_{peak}
V_{IOTM}	Highest Allowable Over Voltage	6000			V_{peak}
	External Creepage	7			mm
	External Clearance	7			mm
	Insulation Thickness	0.5			mm
RIO	Insulation Resistance at T_s , $V_{IO} = 500\text{V}$	10^9			Ω

Typical Performance Curves

Fig. 1 LED Forward Voltage vs. Forward Current

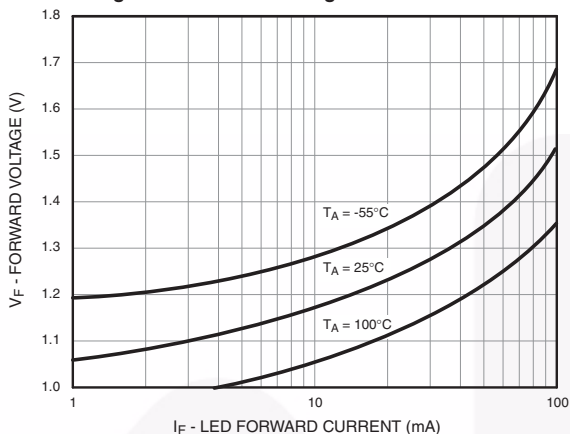


Fig. 2 Normalized CTR vs. Forward Current

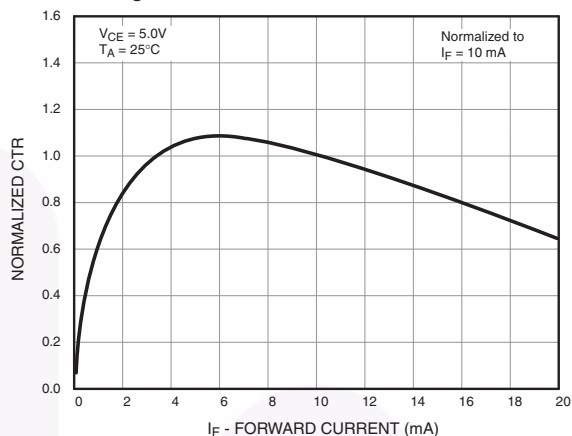


Fig. 3 Normalized CTR vs. Ambient Temperature

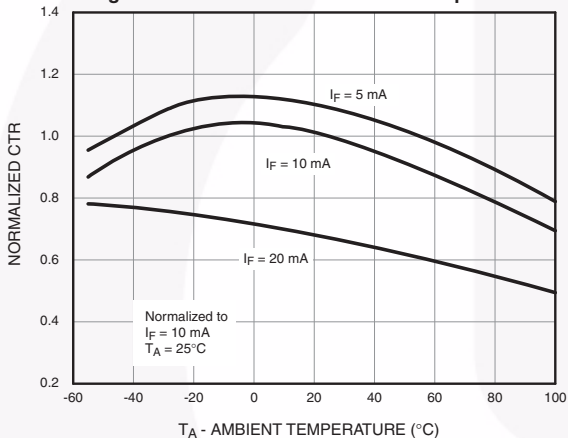


Fig. 4 CTR vs. RBE (Unsaturated)

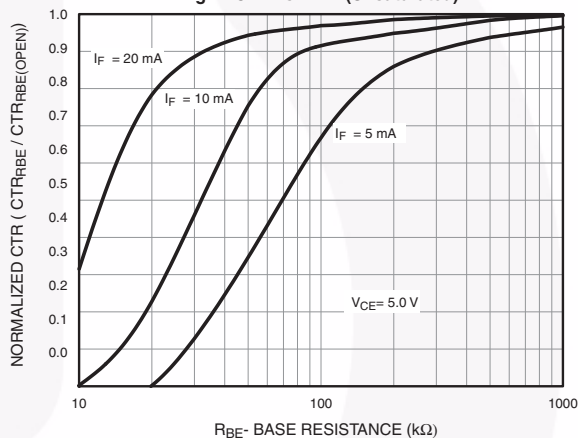


Fig. 5 CTR vs. RBE (Saturated)

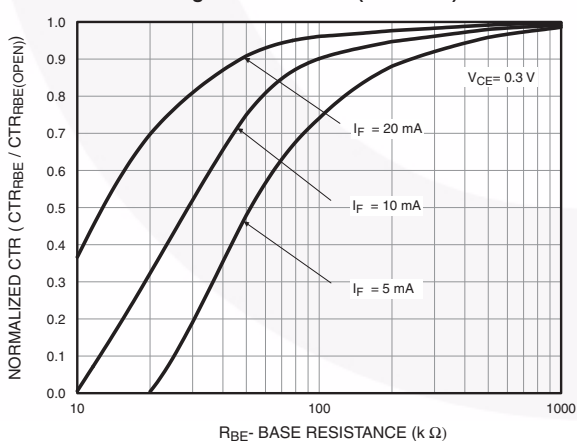
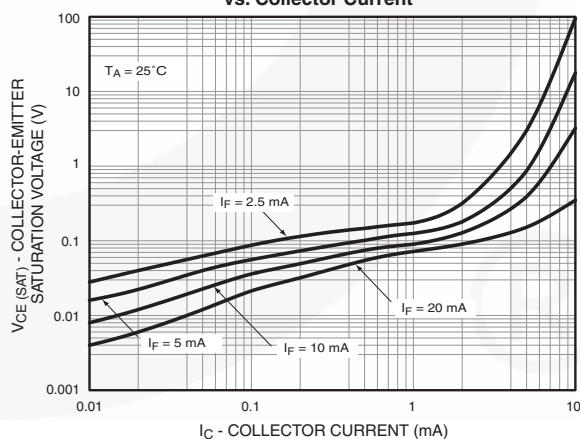


Fig. 6 Collector-Emitter Saturation Voltage vs. Collector Current



Typical Performance Curves (Continued)

Fig. 7 Switching Speed vs. Load Resistor

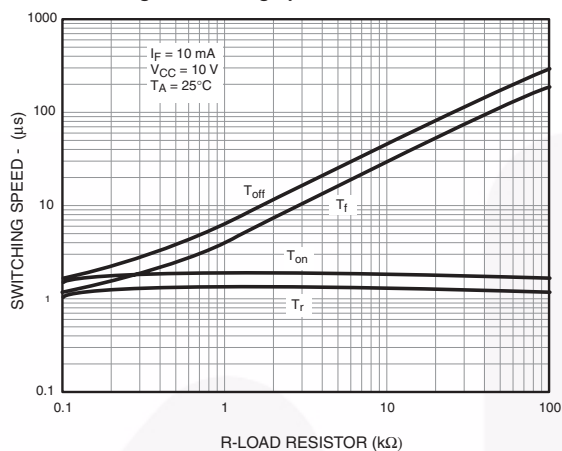


Fig. 8 Normalized t_{on} vs. R_{BE}

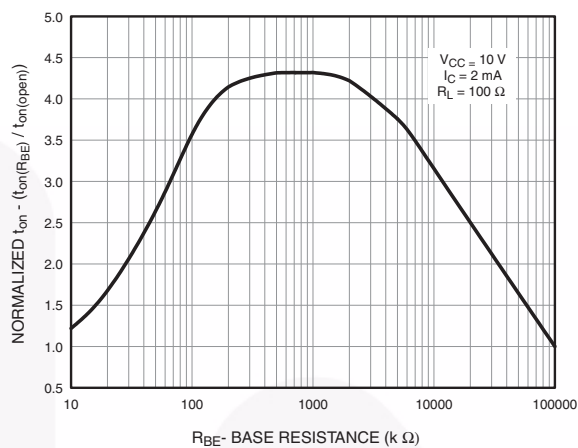


Fig. 9 Normalized t_{off} vs. R_{BE}

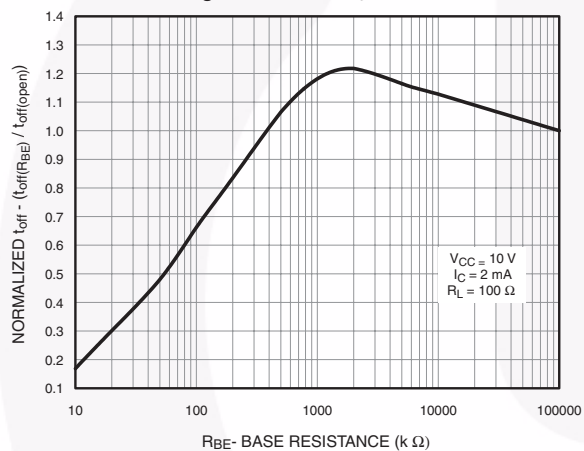
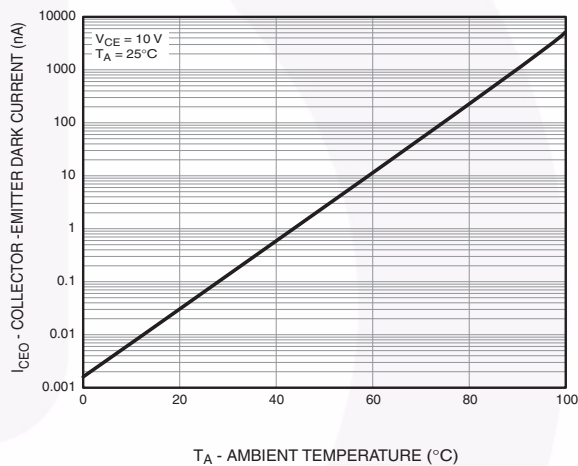
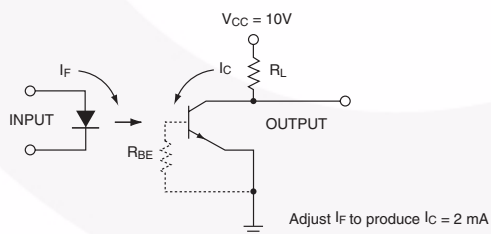


Fig. 10 Dark Current vs. Ambient Temperature



TEST CIRCUIT



WAVE FORMS

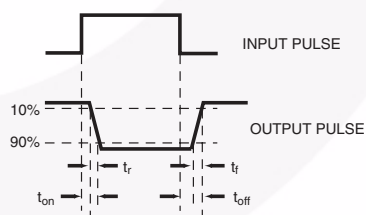
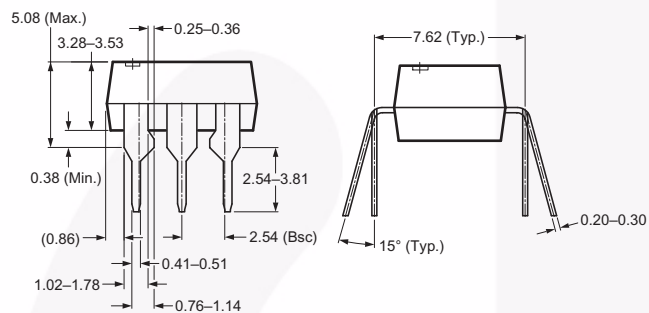
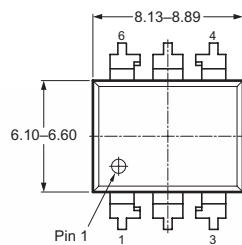


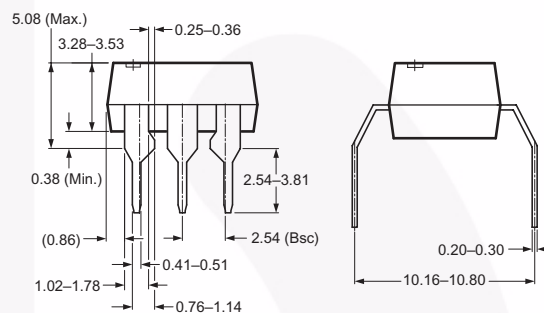
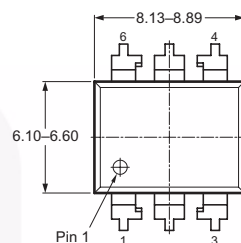
Figure 11. Switching Time Test Circuit and Waveforms

Package Dimensions

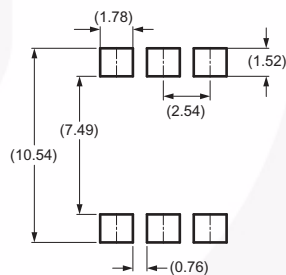
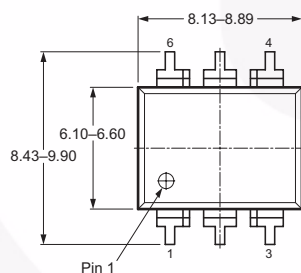
Through Hole



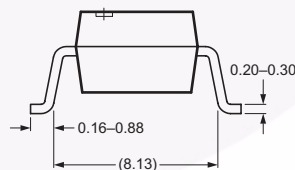
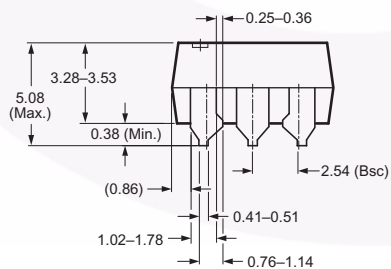
0.4" Lead Spacing



Surface Mount



Recommended Pad Layout

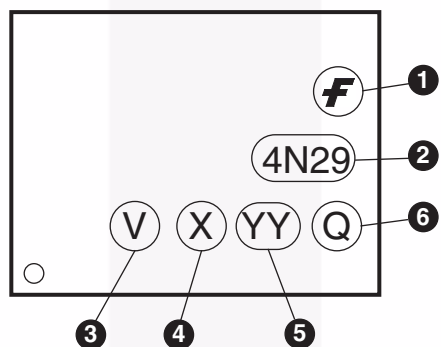


Note:
All dimensions in mm.

Ordering Information

Suffix	Example	Option
No Suffix	4N32M	Standard Through Hole Device (50 units per tube)
S	4N32SM	Surface Mount Lead Bend
SR2	4N32SR2M	Surface Mount; Tape and Reel (1,000 units per reel)
T	4N32TM	0.4" Lead Spacing
V	4N32VM	VDE 0884
TV	4N32TVM	VDE 0884, 0.4" Lead Spacing
SV	4N32SVM	VDE 0884, Surface Mount
SR2V	4N32SR2VM	VDE 0884, Surface Mount, Tape & Reel (1,000 units per reel)

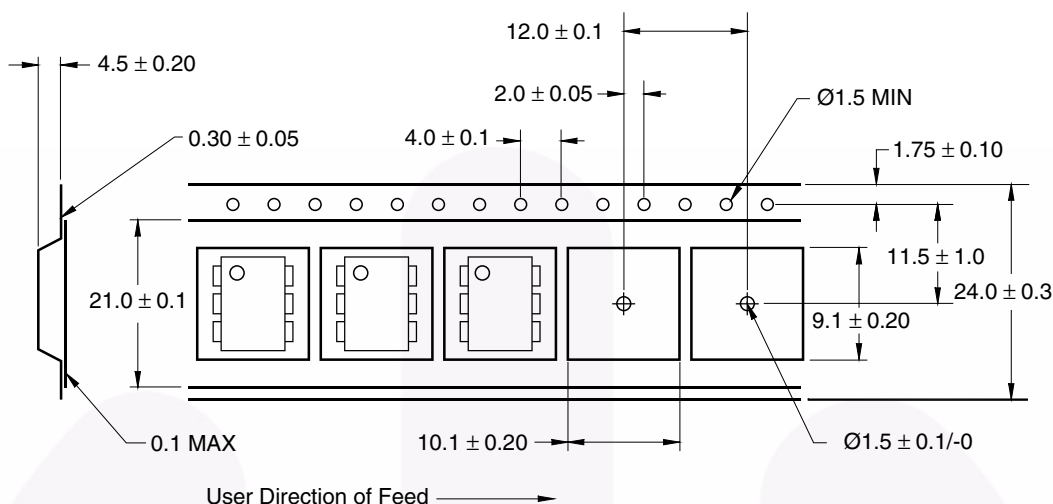
Marking Information



Definitions

1	Fairchild logo
2	Device number
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)
4	One digit year code, e.g., '7'
5	Two digit work week ranging from '01' to '53'
6	Assembly package code

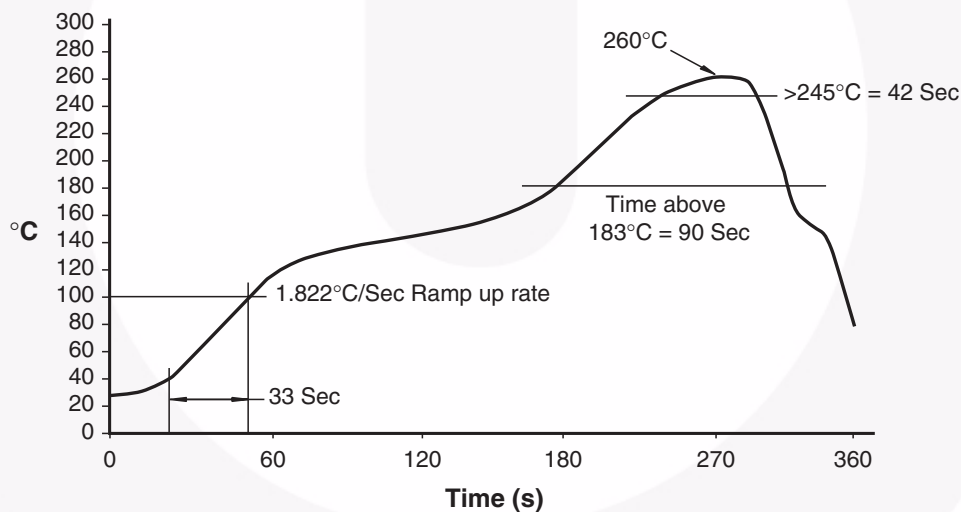
Tape Dimensions



Note:

All dimensions are in millimeters.

Reflow Soldering Profile



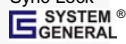


TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

Auto-SPM™
Build it Now™
CorePLUS™
CorePOWER™
CROSSVOLT™
CTL™
Current Transfer Logic™
EcoSPARK®
EfficientMax™
EZSWITCH™*
™*
®
Fairchild®
Fairchild Semiconductor®
FACT Quiet Series™
FACT®
FAST®
FastvCore™
FETBench™
FlashWriter®*
FPS™

F-PFS™
FRFET®
Global Power Resource™
Green FPS™
Green FPS™ e-Series™
Gmax™
GTO™
IntelliMAX™
ISOPLANAR™
MegaBuck™
MICROCOUPLER™
MicroFET™
MicroPak™
MillerDrive™
MotionMax™
Motion-SPM™
OPTOLOGIC®
OPTOPLANAR®
®
PDP SPM™
Power-SPM™

PowerTrench®
PowerXS™
Programmable Active Droop™
QFET®
QS™
Quiet Series™
RapidConfigure™
™
Saving our world, 1mW/W/kW at a time™
SmartMax™
SMART START™
SPM®
STEALTH™
SuperFET™
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SupreMOS™
SyncFET™
Sync-Lock™
 SYSTEM GENERAL

The Power Franchise®
the power franchise
TinyBoost™
TinyBuck™
TinyLogic®
TINYOPTO™
TinyPower™
TinyPWM™
TinyWire™
TriFault Detect™
TRUECURRENT™*
μSerDes™
 SerDes®
UHC®
Ultra FRFET™
UniFET™
VCX™
VisualMax™
XS™

* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I40